

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1919	trench same polysilicon same (dielectric or glass) and anneal\$3 and oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/05 10:34
S2	236	trench same polysilicon same (dielectric or glass) same anneal\$3 same oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 13:28
S3	4550	257/520,E21.545,E21.546,E21.572,E21.55,E21.551,E21.564.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/05 10:40
S4	19	S2 and S3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 13:13
S5	204	S1 and S3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 13:13
S6	168	trench same polysilicon same (dielectric or glass) same anneal\$3 same oxide and (polysilicon with trench)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 13:28
S7	17	S6 and S3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 14:31
S8	592	polysilicon with liner	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 14:32
S9	298	(polysilicon with liner) same trench	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 14:32

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S10	89	S9 and S3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 14:32
S11	233	(polysilicon with liner) same trench same oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 15:06
S12	69	S11 and S3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 14:32
S13	12	(polysilicon adj liner) same trench same oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 15:06
S14	6	(US-20050184356-\$ or US-20040180510-\$ or US-20040038495-\$ or US-20030040189-\$ or US-20050133846-\$).did. or (US-6709924-\$).did.	US-PGPUB; USPAT	OR	ON	2005/09/06 16:10
S15	3	((US-20050184356-\$ or US-20040180510-\$ or US-20040038495-\$ or US-20030040189-\$ or US-20050133846-\$).did. or (US-6709924-\$).did.) and glass	US-PGPUB; USPAT	OR	ON	2005/09/06 16:10
S16	185	trench and ((polysilicon adj layer) with trench) same (angstroms or ".angstrom." or nm or nanometers) and isolation and substrate and anneal\$3 and etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/05 10:42
S17	4747	257/520,E21.545,E21.546,E21. 572,E21.55,E21.551,E21.564.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/05 10:40
S18	13	S16 and S17	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/05 10:40

## EAST Search History

S20	14	trench and ((polysilicon adj layer) with trench) same (angstroms or ".angstrom." or nm or nanometers) and isolation and substrate and anneal\$3 and etch\$3 and (((spin or "spin-on") adj glass) or sog)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/05 10:51
S21	2	"20040180510".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/05 12:19